

Silicon PNP Power Transistors

2SB757

DESCRIPTION

- With TO-3PN package
- High collector current
- Wide area of safe operation
- Complement to type 2SD847

APPLICATIONS

- Audio amplifications
- Serie regulators
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

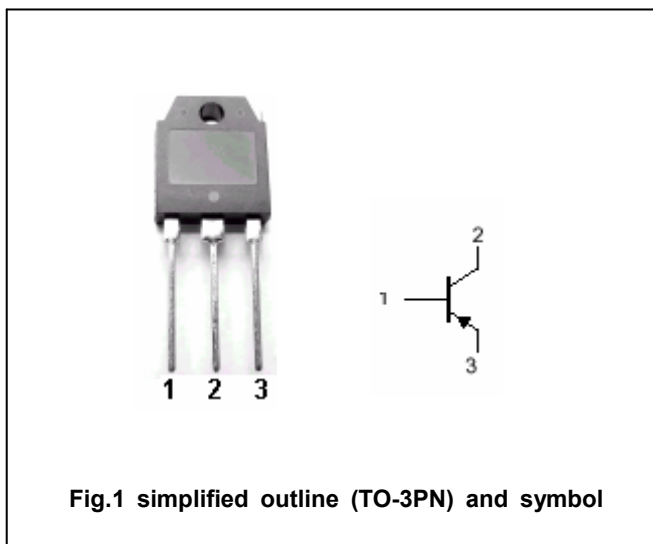


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS (T_C=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-40	V
V _{CEO}	Collector-emitter voltage	Open base	-40	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-15	A
I _B	Base current		-5	A
P _C	Collector power dissipation	T _C =25□	80	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{thj-c}	Thermal resistance from junction to case	1.56	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-0.1mA; I _E =0	-40			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-40			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.1mA; I _C =0	-5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-0.8	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-5A ; V _{CE} =-2V	40		240	

Switching times

t _{on}	Turn-on time	I _C =-15A; I _{B1} =-I _{B2} =-1.5A R _L =2Ω; P _W =20μs, Duty≤2%			1.0	μs
t _s	Storage time				2.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

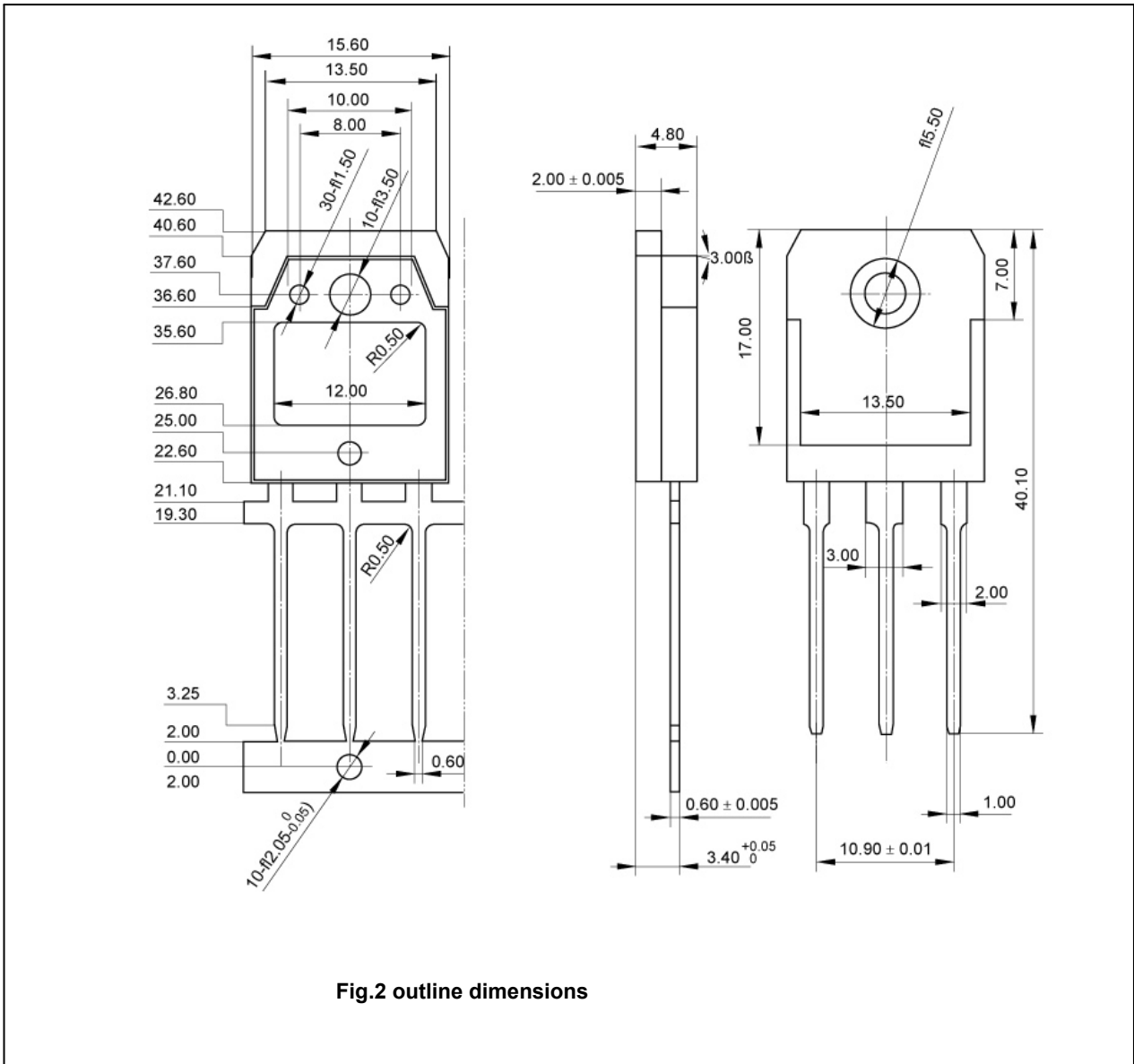


Fig.2 outline dimensions